

40. (Amended) A method of forming a bonding pad for an integrated circuit comprising the steps of:

forming a dielectric layer having first and second opposing faces on an integrated circuit substrate, the dielectric layer including a closed via therein that extends from the first face to the second face and that encloses an inner portion of the dielectric layer, and is enclosed by an outer portion of the dielectric layer, wherein the closed via penetrates the dielectric layer and extends towards the integrated circuit substrate; and

forming a conductive pattern that extends from the first face to the second face in the closed via and on the dielectric layer opposite the substrate.